

# Schottky Diode

$$V_{RRM} = 45\text{ V}$$

$$I_{FAV} = 2 \times 80\text{ A}$$

$$V_F = 0.63\text{ V}$$

High Performance Schottky Diode  
 Low Loss and Soft Recovery  
 Parallel legs

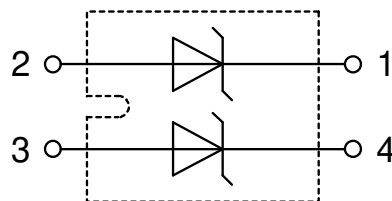
Part number

**DSS2x81-0045B**



Backside: isolated

 E72873



## Features / Advantages:

- Very low  $V_f$
- Extremely low switching losses
- Low  $I_{rm}$  values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

## Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

## Package: SOT-227B (minibloc)

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling

## Disclaimer Notice

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Schottky				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					45	V
$V_{RRM}$	max. repetitive reverse blocking voltage					45	V
$I_R$	reverse current, drain current	$V_R = 45\text{ V}$		$T_{VJ} = 25^\circ\text{C}$		60	mA
		$V_R = 45\text{ V}$		$T_{VJ} = 100^\circ\text{C}$		250	mA
$V_F$	forward voltage drop	$I_F = 80\text{ A}$		$T_{VJ} = 25^\circ\text{C}$		0.65	V
		$I_F = 160\text{ A}$				0.96	V
		$I_F = 80\text{ A}$		$T_{VJ} = 125^\circ\text{C}$		0.63	V
		$I_F = 160\text{ A}$				0.96	V
$I_{FAV}$	average forward current	$T_C = 85^\circ\text{C}$	rectangular	$T_{VJ} = 150^\circ\text{C}$		80	A
$V_{F0}$	threshold voltage	} for power loss calculation only				0.30	V
$r_F$	slope resistance					4	mΩ
$R_{thJC}$	thermal resistance junction to case					0.8	K/W
$R_{thCH}$	thermal resistance case to heatsink					0.1	K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		150	W
$I_{FSM}$	max. forward surge current	$t = 10\text{ ms}; (50\text{ Hz}), \text{ sine}; V_R = 0\text{ V}$		$T_{VJ} = 45^\circ\text{C}$		800	A
$C_J$	junction capacitance	$V_R = 5\text{ V}$	$f = 1\text{ MHz}$	$T_{VJ} = 25^\circ\text{C}$		2.93	nF



Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
$I_{RMS}$	RMS current	per terminal			100	A	
$T_{VJ}$	virtual junction temperature		-40		150	°C	
$T_{op}$	operation temperature		-40		125	°C	
$T_{stg}$	storage temperature		-40		150	°C	
<b>Weight</b>					30	g	
$M_D$	mounting torque		1.1		1.5	Nm	
$M_T$	terminal torque		1.1		1.5	Nm	
$d_{Spp/App}$	creepage distance on surface   striking distance through air	terminal to terminal	10.5	3.2		mm	
$d_{Spb/Apb}$		terminal to backside	8.6	6.8		mm	
$V_{ISOL}$	isolation voltage	t = 1 second		3000		V	
		t = 1 minute	50/60 Hz, RMS; $I_{ISOL} \leq 1$ mA	2500		V	

**Product Marking**



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSS2x81-0045B	DSS2x81-0045B	Tube	10	470422

**Equivalent Circuits for Simulation**

\* on die level

$T_{VJ} = 150^{\circ}C$



Schottky

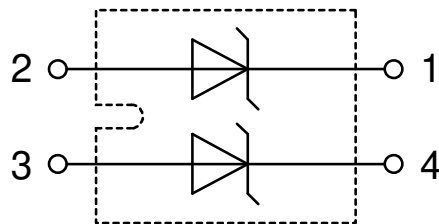
$V_{0\ max}$	threshold voltage	0.3	V
$R_{0\ max}$	slope resistance *	2.2	mΩ



**Outlines SOT-227B (minibloc)**



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



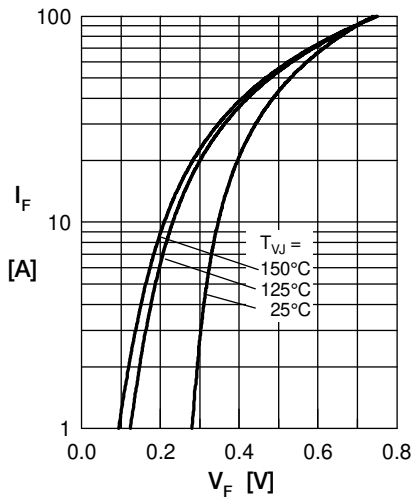
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Fig. 1 Max. forward voltage drop characteristics

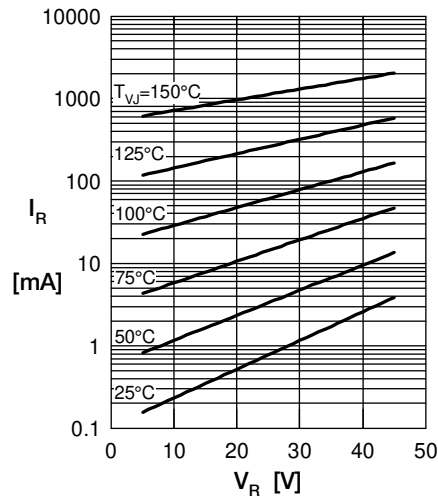
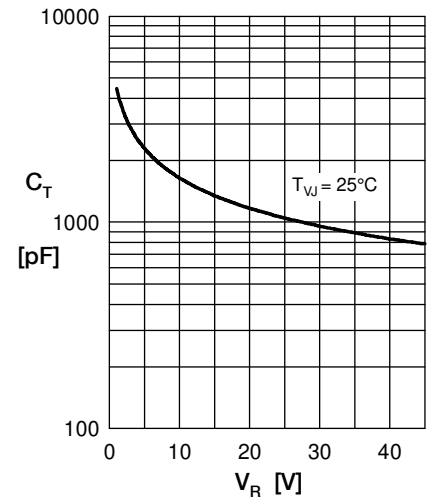
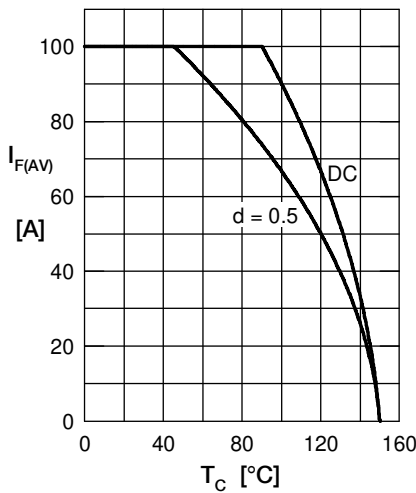
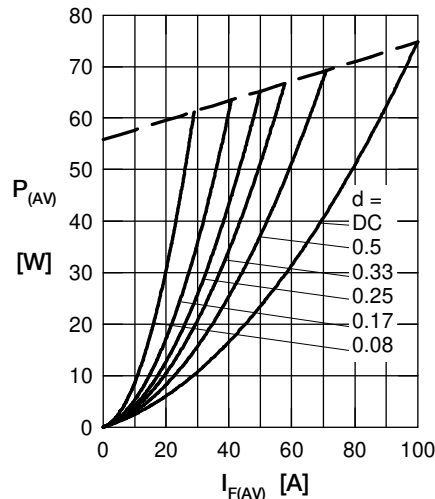

 Fig. 2 Typ. reverse current  $I_R$  vs. reverse voltage  $V_R$ 

 Fig. 3 Typ. junction capacitance  $C_T$  vs. reverse voltage  $V_R$ 

 Fig. 4 Average forward current  $I_{F(AV)}$  vs. case temp.  $T_C$ 


Fig. 5 Forward power loss characteristics

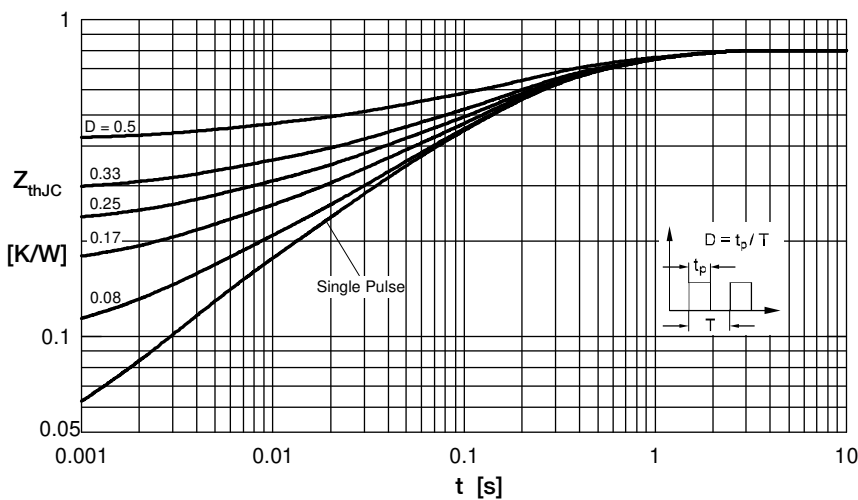


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode